

June 2014

FDA18N50

N-Channel UniFETTM MOSFET 500 V, 19 A, 265 m Ω

Features

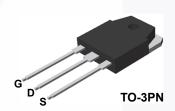
- $R_{DS(on)}$ = 265 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

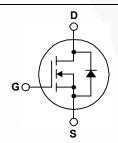
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA18N50	Unit
V _{DSS}	Drain-Source Voltage			500	V
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		19 11.4	A A
I _{DM}	Drain Current	- Pulsed	(Note 1)	76	Α
V _{GSS}	Gate-Source voltage			±30	V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	945	mJ
AR	Avalanche Current		(Note 1)	19	А
E _{AR}	Repetitive Avalanche Energy		(Note 1)	23	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		239 1.92	W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FDA18N50	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/VV	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	500			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V V _{DS} = 400V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	-		-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 9.5A		0.220	0.265	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 40V, I_{D} = 9.5A$			25		S
Dynamic C	haracteristics			II.		
C _{iss}	Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz		2200	2860	pF
C _{oss}	Output Capacitance			330	430	pF
C _{rss}	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics				1	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 250V, I_D = 19A$ $R_G = 25\Omega$ (Note 4)		55	120	ns
t _r	Turn-On Rise Time			165	340	ns
t _{d(off)}	Turn-Off Delay Time			95	200	ns
t _f	Turn-Off Fall Time			90	190	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 19A		45	60	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V	-	12.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sour	rce Diode Characteristics and Maximus	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				19	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				76	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 19A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 19A		500		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		5.4		μС

NOTES:

 $^{{\}bf 1.}\ {\bf Repetitive}\ {\bf Rating:}\ {\bf Pulse}\ {\bf width}\ {\bf limited}\ {\bf by}\ {\bf maximum}\ {\bf junction}\ {\bf temperature}$

^{2.} L = 4.7mH, I $_{AS}$ = 19A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C

^{3.} $I_{SD} \le 19 A$, di/dt $\le 200 A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting T_J = $25^{\circ}C$

^{4.} Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

Figure 1. On-Region Characteristics

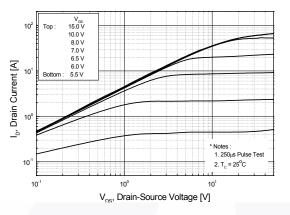


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

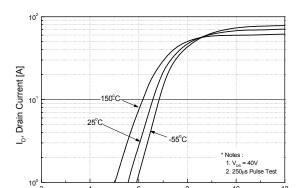


Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

V_{GS}, Gate-Source Voltage [V]

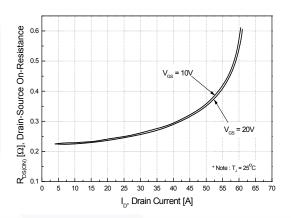


Figure 5. Capacitance Characteristics

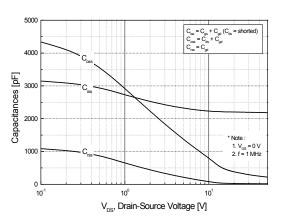
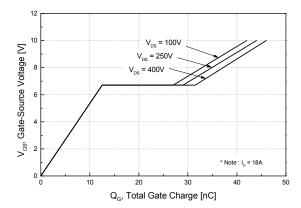


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

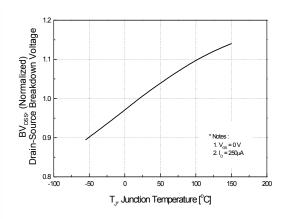


Figure 8. On-Resistance Variation vs. Temperature

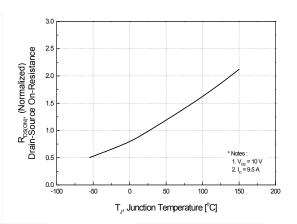


Figure 9. Maximum Safe Operating Area

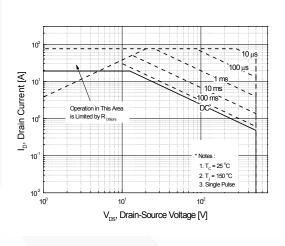


Figure 10. Maximum Drain Current vs. Case Temperature

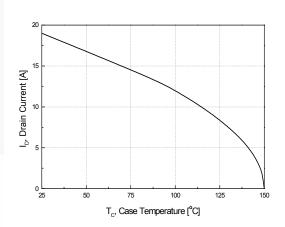


Figure 11. Transient Thermal Response Curve

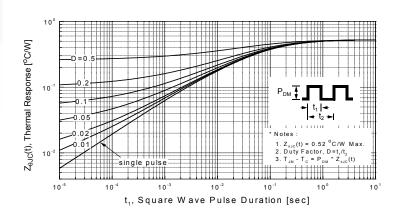


Figure 12. Gate Charge Test Circuit & Waveform

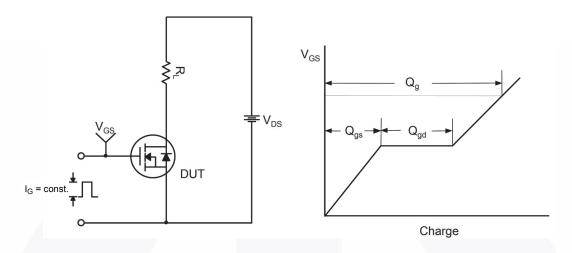


Figure 13. Resistive Switching Test Circuit & Waveforms

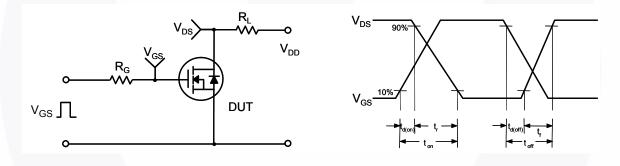
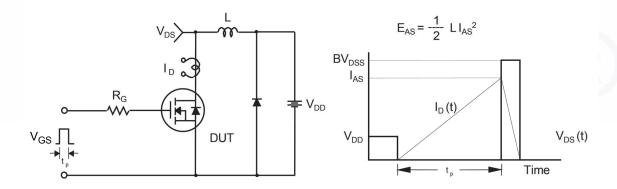


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



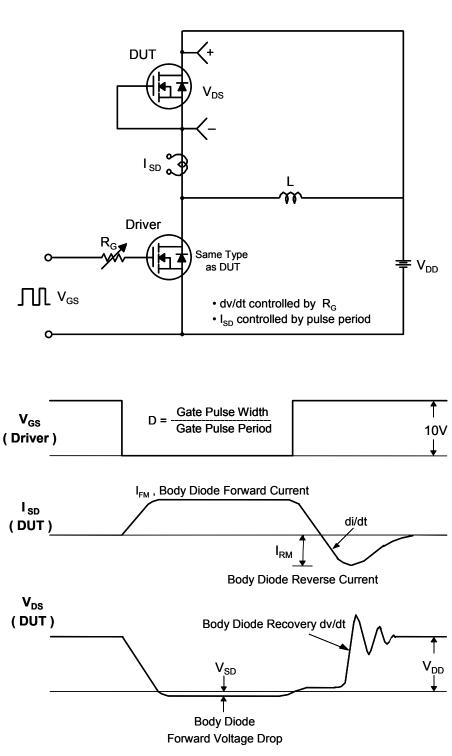
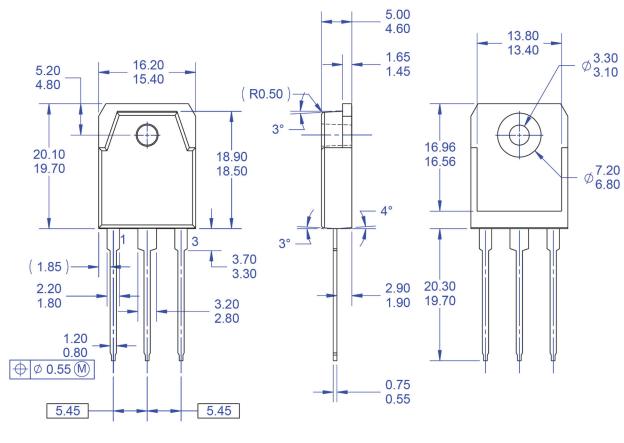
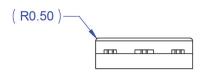


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

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 E) DRAWING FILE NAME: TO3PN03AREV1.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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